



## AO4468

### N-Channel Enhancement Mode Field Effect Transistor

#### General Description

The AO4468 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

Standard Product AO4468 is Pb-free (meets ROHS & Sony 259 specifications). AO4468L is a Green Product ordering option. AO4468 and AO4468L are electrically identical.

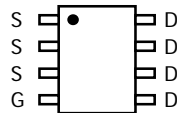
#### Features

$$V_{DS} (V) = 30V$$

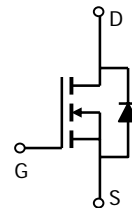
$$I_D = 11.6A \quad (V_{GS} = 10V)$$

$$R_{DS(ON)} < 14m\Omega \quad (V_{GS} = 10V)$$

$$R_{DS(ON)} < 22m\Omega \quad (V_{GS} = 4.5V)$$



SOIC-8



#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	11.6	A
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		9.2	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	50	
Power Dissipation	$P_D$	3.1	W
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		2	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

#### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	59	75	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$
Steady-State				

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C		0.003	1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =10mA	1.5	2	3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	50			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =11.6A T <sub>J</sub> =125°C		11 17	14 21	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		17.4	22	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =11.6A		19		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.73	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				4.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		955	1200	pF
C <sub>oss</sub>	Output Capacitance			145		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			112		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		0.5	0.85	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =11.6A		17	24	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			9	12	nC
Q <sub>gs</sub>	Gate Source Charge			3.4		nC
Q <sub>gd</sub>	Gate Drain Charge			4.7		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.30Ω, R <sub>GEN</sub> =3Ω		5	6.5	ns
t <sub>r</sub>	Turn-On Rise Time			6	7.5	ns
t <sub>D(off)</sub>	Turn-Off DelayTime			19	25	ns
t <sub>f</sub>	Turn-Off Fall Time			4.5	6	ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =11.6A, dI/dt=100A/μs		19	21	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =11.6A, dI/dt=100A/μs		9	12	nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t<sub>θJA</sub> ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

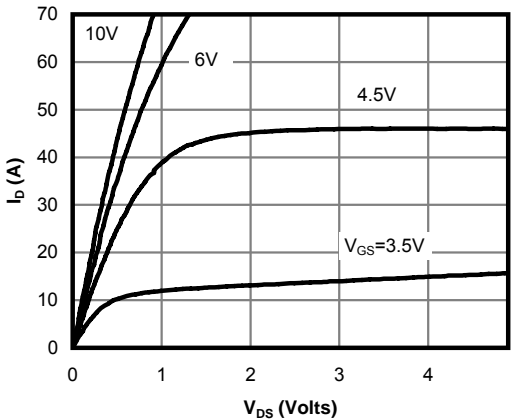


Fig 1: On-Region Characteristics

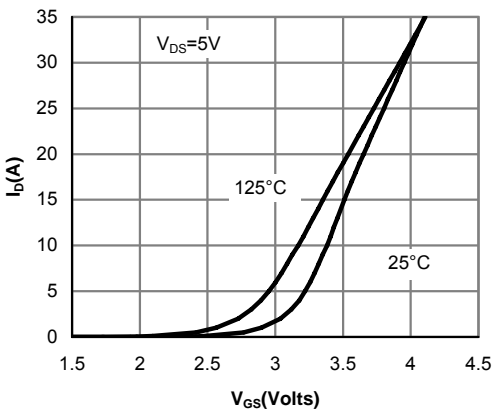


Figure 2: Transfer Characteristics

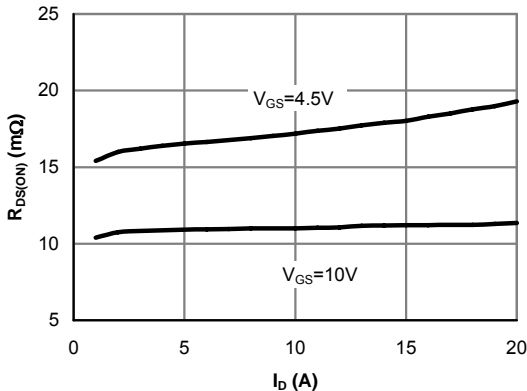


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

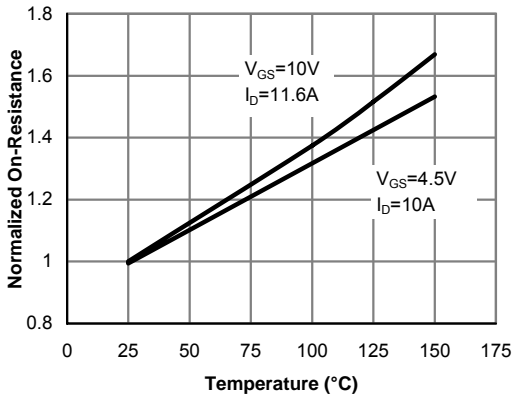


Figure 4: On-Resistance vs. Junction Temperature

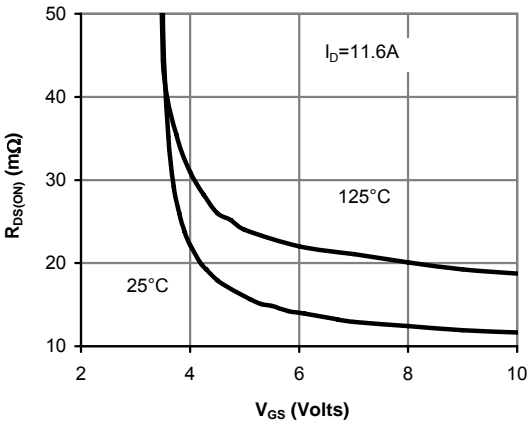


Figure 5: On-Resistance vs. Gate-Source Voltage

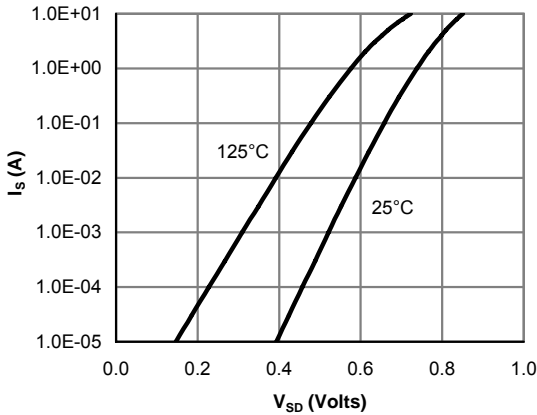


Figure 6: Body-Diode Characteristics

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